

General Description

The WST6004 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WST6004 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- High-speed switching
- Green Device Available

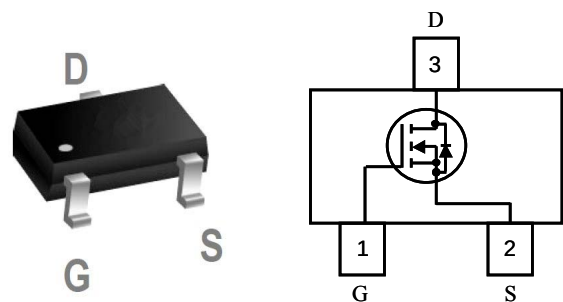
Product Summary

BVDSS	RDSON	ID
20V	140mΩ	0.6A

Applications

- Replace Digital Transistor
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

SOT-523 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 8	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	600	mA
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	300	mA
I_{DM}	Pulsed Drain Current ²	3	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	0.175	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	625	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.05	---	V/ $^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=4.5V$, $I_D=0.6A$	---	140	450	m Ω
		$V_{GS}=2.5V$, $I_D=0.5A$	---	180	765	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	0.35	---	1.0	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-3.7	---	mV/ $^{\circ}\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=16V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=16V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 8V$, $V_{DS}=0V$	---	---	± 10	μA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=0.1A$	---	880	---	mS
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V$, $V_{GS}=10V$, $R_G=3.3\Omega$, $I_D=0.1A$	---	6	---	ns
T_r	Rise Time		---	3.8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	28	---	
T_f	Fall Time		---	18	---	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1MHz$	---	130	---	pF
C_{oss}	Output Capacitance		---	20	---	
C_{rss}	Reverse Transfer Capacitance		---	16	---	

Diode Characteristics

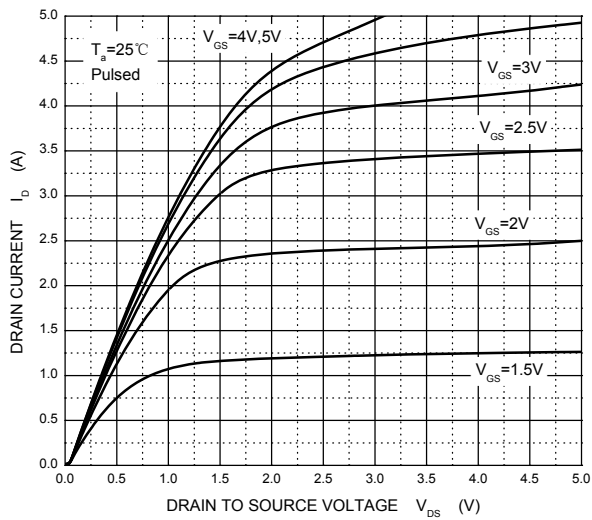
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	100	mA
I_{SM}	Pulsed Source Current ^{2,4}		---	---	0.5	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=0.2A$, $T_J=25^{\circ}\text{C}$	---	---	1	V

Note :

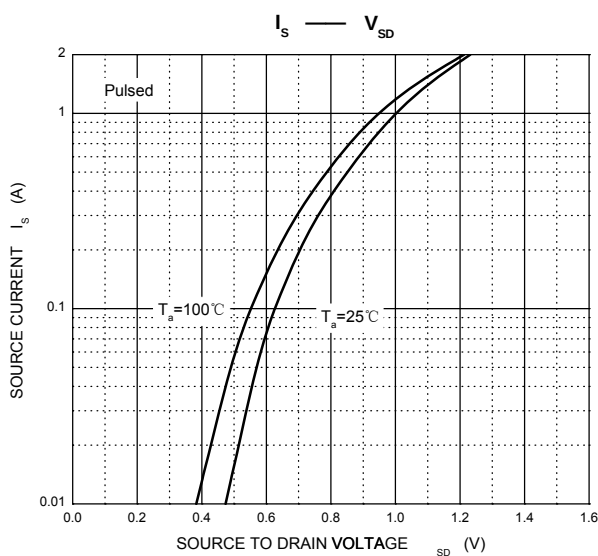
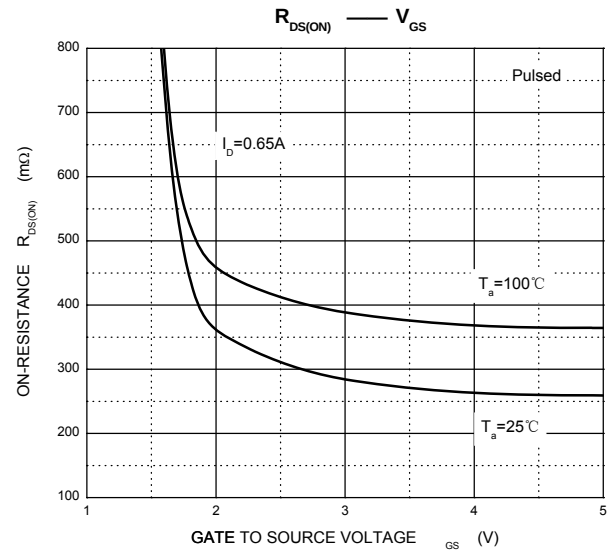
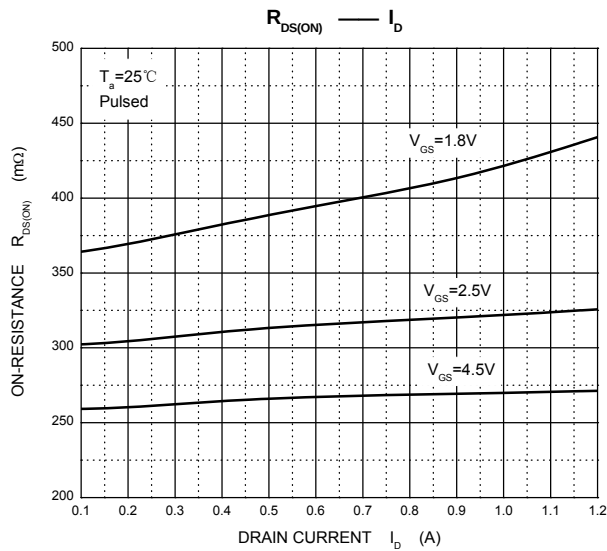
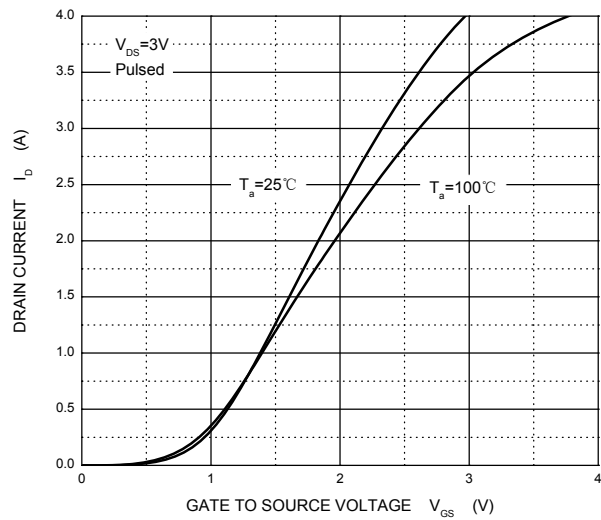
- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature.
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Performance Characteristics

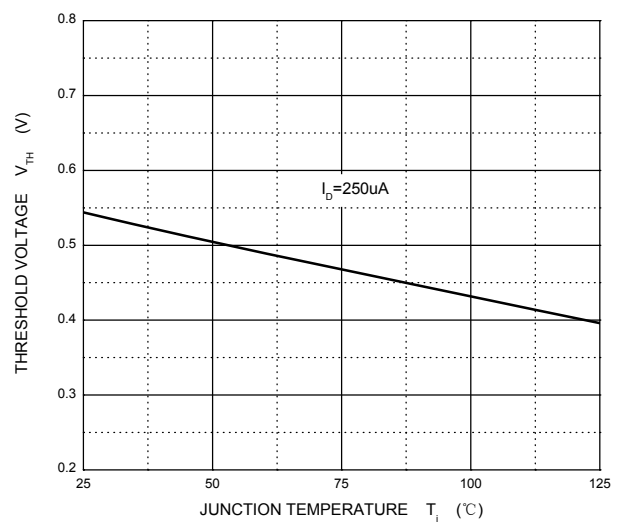
Output Characteristics



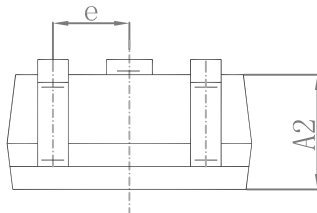
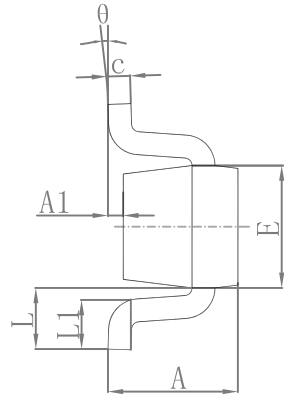
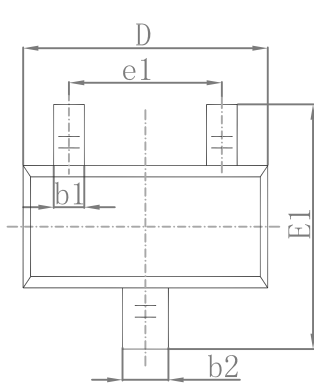
Transfer Characteristics



Threshold Voltage

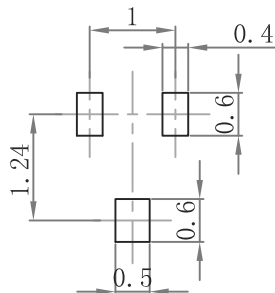


SOT-523 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
K	0°	8°	0°	8°

SOT-523 Suggested Pad Layout



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